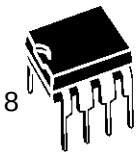
SGS-THOMSON MICROELECTRONICS

ST93C46A,46C,46T
ST93C47C,47T

SERIAL MICROWIRE BUS 1K (64 x 16 or 128 x 8) EEPROM

DATA BRIEFING

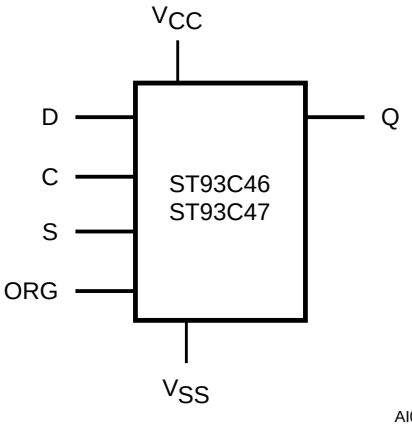
- 1 MILLION ERASE/WRITE CYCLES, with 40 YEARS DATA RETENTION
- DUAL ORGANIZATION: 64 x 16 or 128 x 8
- BYTE/WORD and ENTIRE MEMORY PROGRAMMING INSTRUCTIONS
- SELF-TIMED PROGRAMMING CYCLE with AUTO-ERASE
- READY/BUSY SIGNAL DURING PROGRAMMING
- SINGLE SUPPLY VOLTAGE:
  - 4.5V to 5.5V for ST93C46 version
  - 3V to 5.5V for ST93C47 version
- SEQUENTIAL READ OPERATION
- 5ms TYPICAL PROGRAMMING TIME
- ENHANCED ESD/LATCH UP PERFORMANCE for "C" VERSION



PSDIP8 (B)
0.4mm Frame

SO8 (M)
150mil Width

Logic Diagram

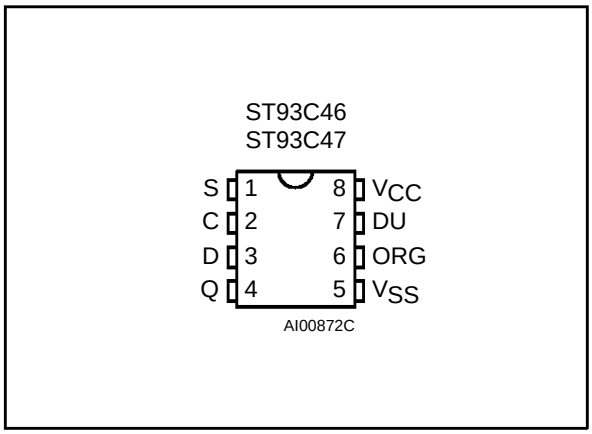


DESCRIPTION

This specification covers a range of 1K bit serial EEPROM products, the ST93C46A,46C,46T specified at 5V±10% and the ST93C47C,47T specified at 3V to 5.5V.

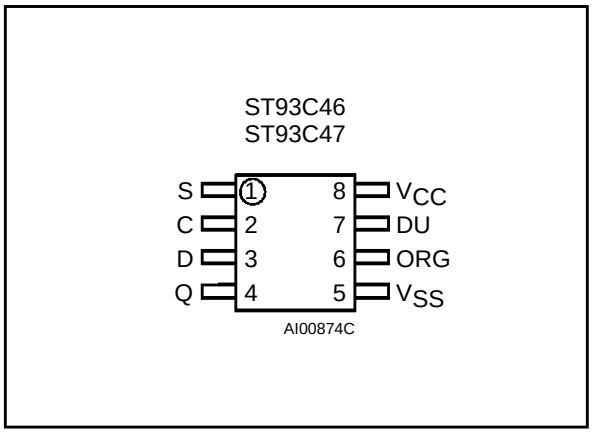
In the text, products are referred to as ST93C46. The ST93C46 is a 1K bit Electrically Erasable Programmable Memory (EEPROM) fabricated with SGS-THOMSON's High Endurance Single Polysilicon CMOS technology. The memory is accessed through a serial input (D) and output (Q).

DIP Pin Connections



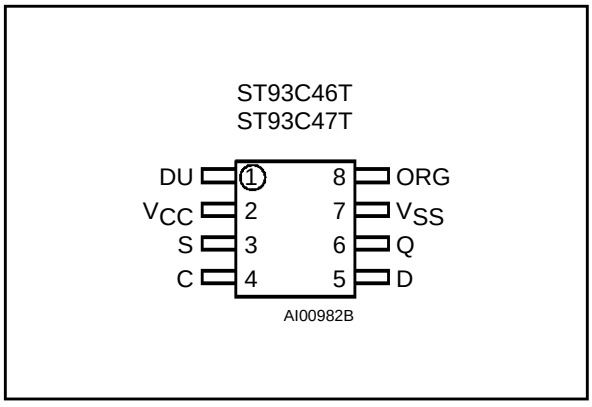
Warning: DU = Don't Use

SO Pin Connections



Warning: DU = Don't Use

SO, 90° Turn, Pin Connections



Warning: DU = Don't Use

Signal Names

S	Chip Select Input
D	Serial Data Input
Q	Serial Data Output
C	Serial Clock
ORG	Organisation Select
V_{CC}	Supply Voltage
V_{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.
For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: ST93C46A M 1 013TR

Operating Voltage

- 46 4.5V to 5.5V
- 47 3V to 5.5V

Revision

- A CMOS F3
- C CMOS F4
- T CMOS F3 90° Turn pin out

Package

- B PSDIP8 0.4mm Frame
- M SO8 150mil Width

Temp. Range

- 1 0 to 70 °C
- 6 –40 to 85 °C
- 3 –40 to 125 °C

Option

- 013TR Tape & Reel Packing (A, T ver.)
- TR Tape & Reel Packing (C version)